February 2000

# FDD6670A

## FAIRCHILD SEMICONDUCTOR

# FDD6670A

## N-Channel, Logic Level, PowerTrench® MOSFET

#### **General Description**

This N-Channel Logic level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

#### Applications

- DC/DC converter
- Motor drives

### Features

• 66 A, 30 V. 
$$R_{DS(on)} = 0.008 \ \Omega @ V_{GS} = 10 V$$
  
 $R_{DS(on)} = 0.010 \ \Omega @ V_{GS} = 4.5 V.$ 

- Low gate charge (35nC typical).
- Fast switching speed.
- High performance trench technology for extremely low R<sub>DS(on)</sub>.





## Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V <sub>DSS</sub>	Drain-Source Voltage	30	V	
V <sub>GSS</sub>	Gate-Source Voltage	<u>±</u> 20	V	
ID	Maximum Drain Current -Continuous (Note 1)	66	A	
	$T_A = 25^{\circ}C  (Note \ 1a)$	15		
	Maximum Drain Current -Pulsed	100		
PD	Maximum Power Dissipation $T_c = 25^{\circ}C$ (Note 1)	70	W	
	$T_A = 25^{\circ}C  (Note \ 1a)$	3.2		
	$T_A = 25^{\circ}C$ (Note 1b)	1.3		
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	۰C	

## **Thermal Characteristics**

R <sub>θ</sub> JC	Thermal Resistance, Junction-to-Case	(Note 1)	1.8	∘C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	(Note 1a)	40	∘C/W
	Thermal Resistance, Junction-to-Ambient	(Note 1b)	96	∘C/W

#### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDD6670A	FDD6670A	13"	16mm	2500

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Symbol	al Characteristics	$T_A = 25^{\circ}C$ unless otherwise noted	T			1
	Parameter	Test Conditions	Min	Тур	Max	Units
Drain-So	urce Avalanche ratings	(Note 2)				
W <sub>DSS</sub>	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 15 \text{ V}, I_D = 66 \text{ A}$			400	mJ
I <sub>AR</sub>	Maximum Drain-Source Avalan	che Current			66	А
Off Chara	cteristics		1			I
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	30			V
<u>A</u> BV⊡ss ∆TJ	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu A$ , Referenced to $25^{\circ}C$		25		mV/∘C
I <sub>DSS</sub>	Zero Gate Voltage Drain	$V_{DS} = 24 \text{ V},  V_{GS} = 0 \text{ V}$			1	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current,	$V_{GS} = 20V, V_{DS} = 0 V$			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V},  V_{DS} = 0 \text{ V}$			-100	nA
On Chara	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	1	1.6	3	V
AVGS(th)	Gate Threshold Voltage	$I_D = 250 \ \mu$ A, Referenced to 25°C		-4		mV/°C
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 15 \text{ A}$ $V_{GS} = 10 \text{ V}, \text{ I}_{D} = 15 \text{ A}, \text{T}_{J} = 125 \text{ °C}$ $V_{CS} = 4.5 \text{ V}, \text{ I}_{D} = 13 \text{ A}$		0.0065 0.0090 0.0085	0.008 0.013 0.010	Ω
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	50	0.0000	0.0.0	Α
<b>g</b> <sub>FS</sub>	Forward Transconductance	$V_{DS} = 5 V, I_D = 12 A$		55		S
Dynamic	Characteristics	-				
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		3200		pF
Coss	Output Capacitance	t = 1.0 MHz		820		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			400		pF
Switchin	a Characteristics (Note 2)					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 15 V, I_{D} = 1 A,$		15	27	ns
tr	Turn-On Rise Time	$V_{GS}$ = 10 V, $R_{GEN}$ = 6 $\Omega$		15	27	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	1		85	105	ns
t <sub>f</sub>	Turn-Off Fall Time			42	68	ns
Q <sub>a</sub>	Total Gate Charge	V <sub>DS</sub> = 15 V. I <sub>D</sub> = 15 A.		35	50	nC
Q <sub>as</sub>	Gate-Source Charge	$V_{GS} = 5 V,$		9		nC
Q <sub>gd</sub>	Gate-Drain Charge			16		nC
Ducin Oc		Detin a				
urain-50	Maximum Continuous Drain-So	<u>s and Waximum Katings</u>			23	Δ
l.	Maximum Continuous Drain-50				2.5	~

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September 1999, Rev. A

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